

DE LA RECHERCHE À L'INDUSTRIE

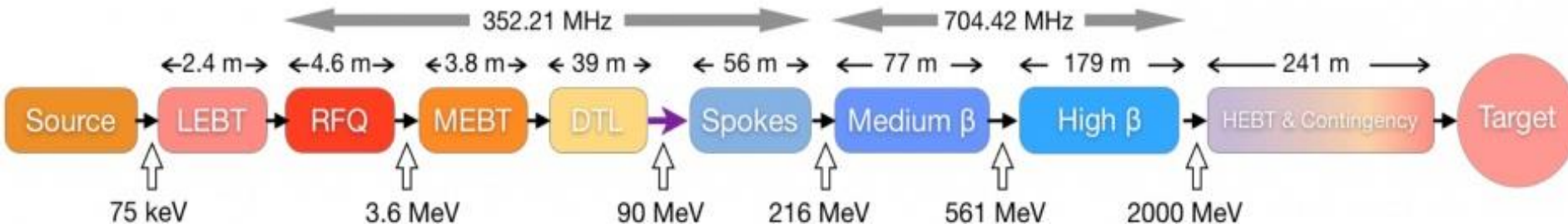


SOURCE SIGNAL ESTIMATION AND READOUT SYSTEMS

ESS-0092071 & ESS-0092072

CEA-ESS-DIA-RP-0016 & CEA-ESS-DIA-RP-0017

Optimus+



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I. Source signal estimation

- a. Model
- b. Assumptions
- c. Results

II. Readout systems

- a. Conductive strips
- b. MCP and conductive strips
- c. MCP, Phosphor Screen and Camera
- d. Silicon pixelated sensor and TimePix3



I. SOURCE SIGNAL ESTIMATION

Ionization

- Goal: estimate the number of ionized ion/electron pairs created

- $$N_{ionization\ pairs} = N_{beam} \cdot \frac{1}{W} \cdot \frac{dE}{dx}$$

- $\frac{dE}{dx}$ → ESS stopping power

- W → Energy to produce a pair

- N_{beam} → Number of protons in one pulse beam

- To quantify the stopping power → Bethe-Bloch

Bethe-Bloch

$$\frac{dE}{dx} = K \cdot \rho \cdot \frac{Z}{A} \cdot \frac{z^2}{\beta^2} \left[\frac{1}{2} \cdot \ln \frac{2 \cdot m_e \cdot (\beta\gamma)^2 \cdot T_{max}}{I^2} - \beta^2 \right]$$

- Stopping power of heavy charged particle in a medium
- Constants
- Medium → Most valuable parameter: density of medium
- Incident particle → Most valuable parameter: energy of particle

Medium: ESS Vacuum

- Perfect gas mixture:
 - 79% H₂
 - 10% CO
 - 10% CO₂
 - 1% N₂
- At 10⁻⁹ mbar → Low density !

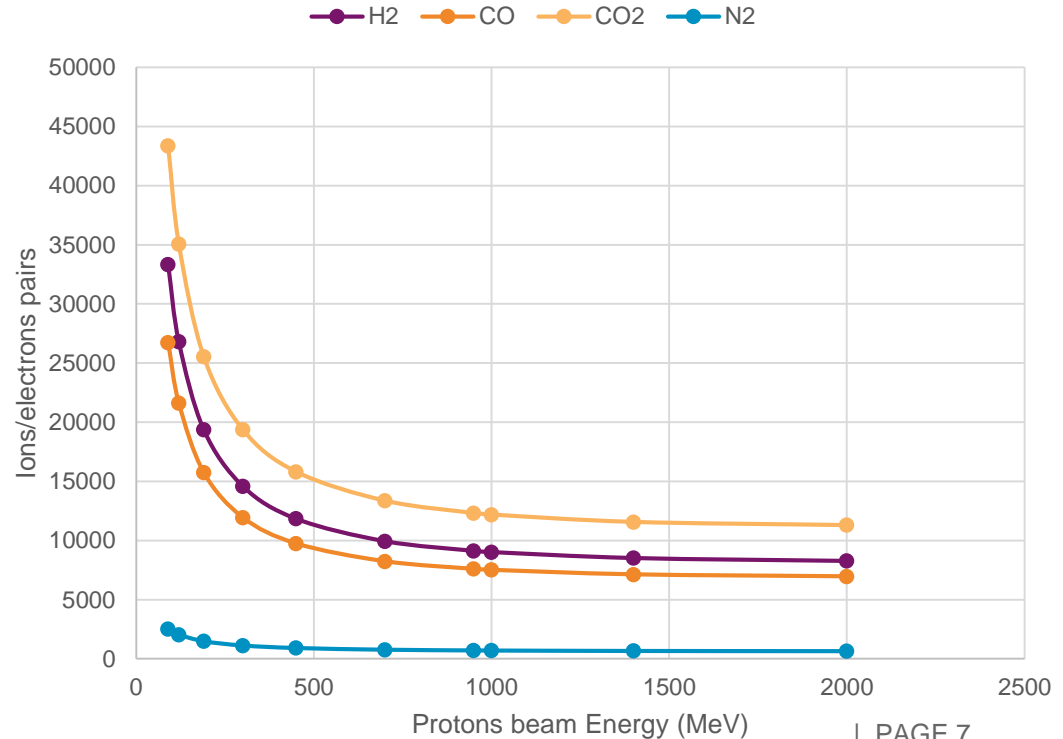
Particle: Protons Beam

- Protons
- From 90MeV to 2GeV
- Pulse length: 2.86ms
- Pulse repetition: 14Hz
- 62.5mA → 10¹⁵ protons per pulse

Energy (MeV)	Ions/Electrons per pulse per cm	Charge (fC)	I(pA)
90	105986	17	5.94
200	60159	9.6	3.35
500	36622	5.87	2
1000	29463	4.72	1.65
1500	27717	4.44	1.54
2000	27224	4.36	1.52

Gas	Proportion %	Contribution %
H ₂	79	30
CO	10	25
CO ₂	10	40
N ₂	1	5

- Signal expected is very low
- Contribution != Proportion
- Independent to readout !





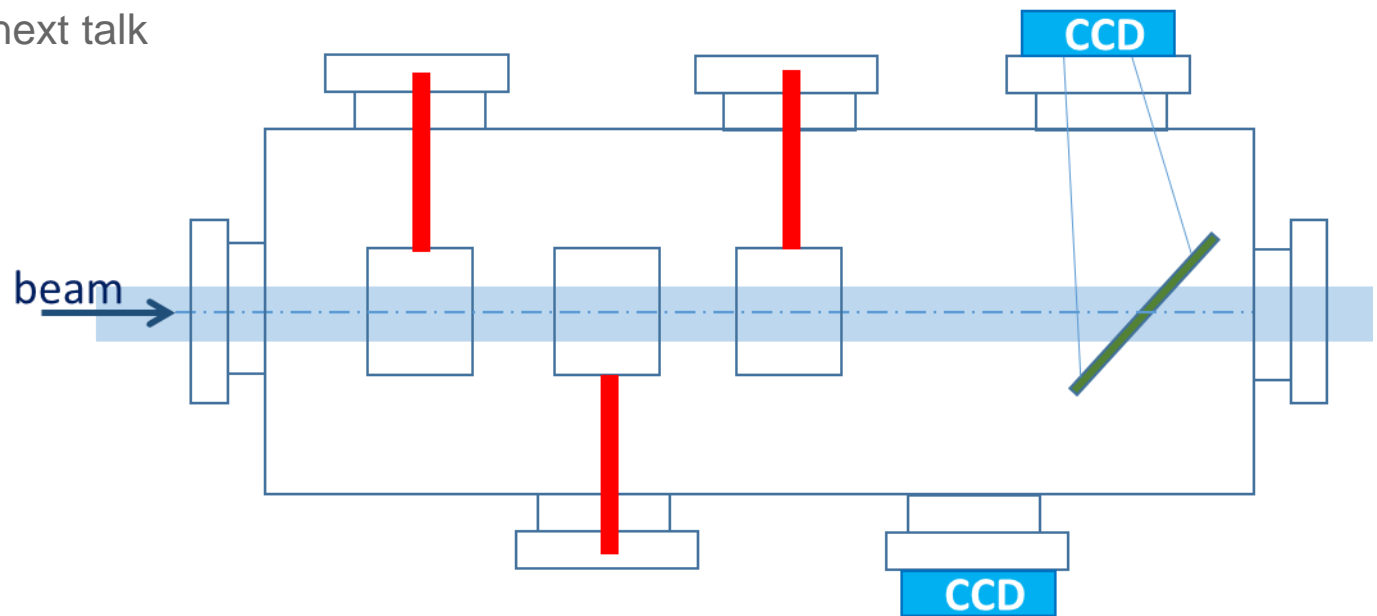
II. READOUT SYSTEMS PRESENTATION

Requirements

- ESS facility → Reliable readout system
 - Radiation hard
 - Ageing of device
 - Low outgassing materials compliant to ESS rules
- Low Signal → High Sensitive readout
 - Measure at beam intensity 62.5 mA down to 6 mA current
- Speed:
 - Pulses (integration)
 - Pulse
 - Bunches (pulse behavior)
- Ions detection → Readout should work either with ions or electrons
- Electronics integration

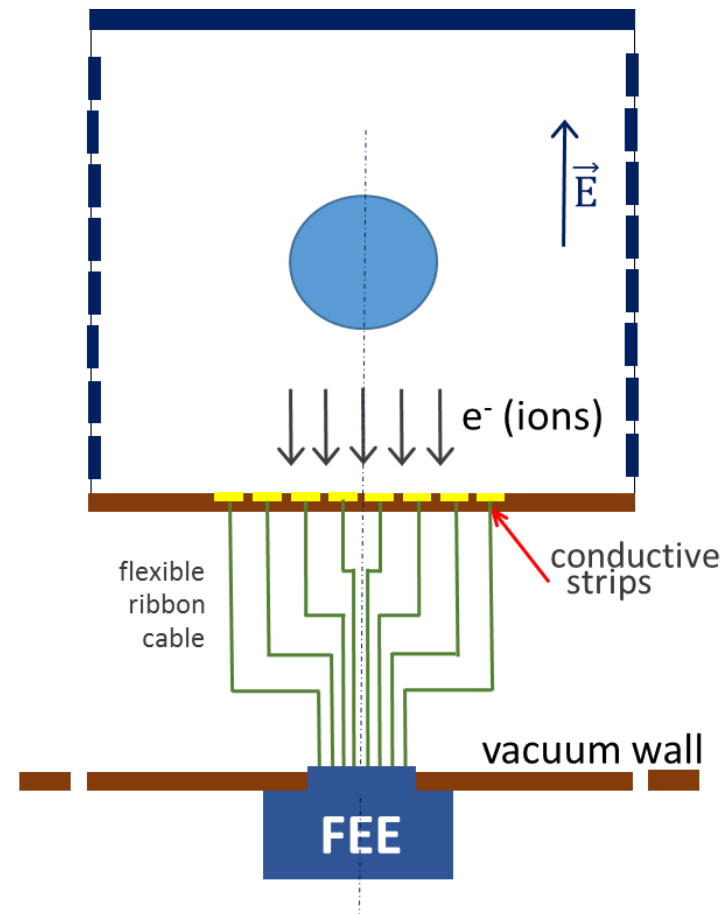
Several readouts

- Many requirements → test several readouts in order to find the best one
- Four interesting readouts have been selected
- We will be able to test several readouts (at least 3) with one test bench
- See more on next talk



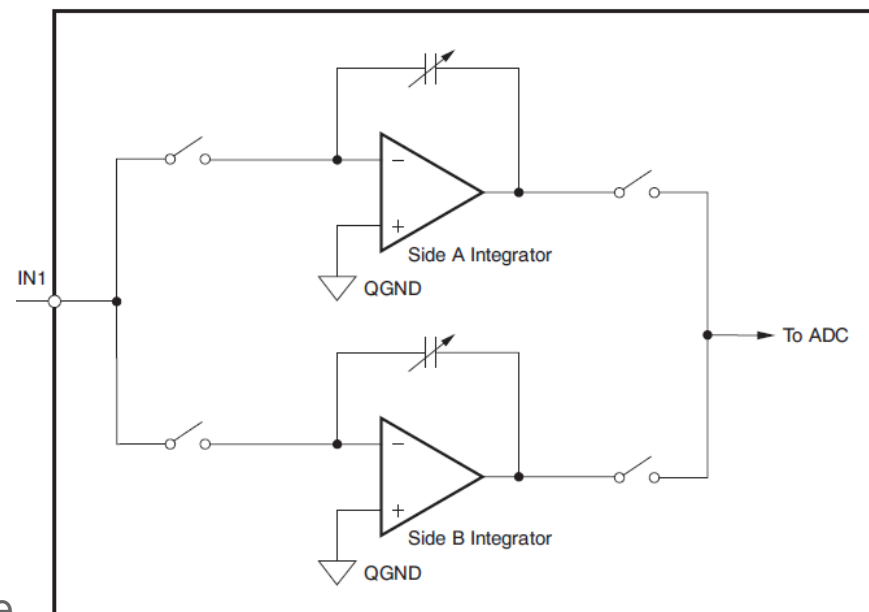
Principle of operation

- Ceramic PCB with conductive strips
- Charge in motion induces current on strips
- Integrator or transimpedance amplification



Electronics

- Existing solution: the DDC chips family from TI
- Double integrator for continuous integration + ADC
- Multichannel (2 up to 64)
- Integration range:
 - Time: 10 μ s to 1s
 - Selectable range: 3pC up to 350pC
 - Noise: few ppm decades of FSR (see next slide)

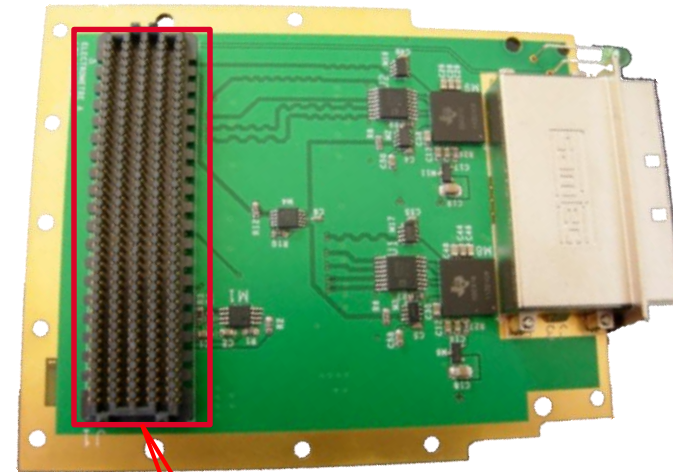


<http://www.ti.com/product/DDC264>

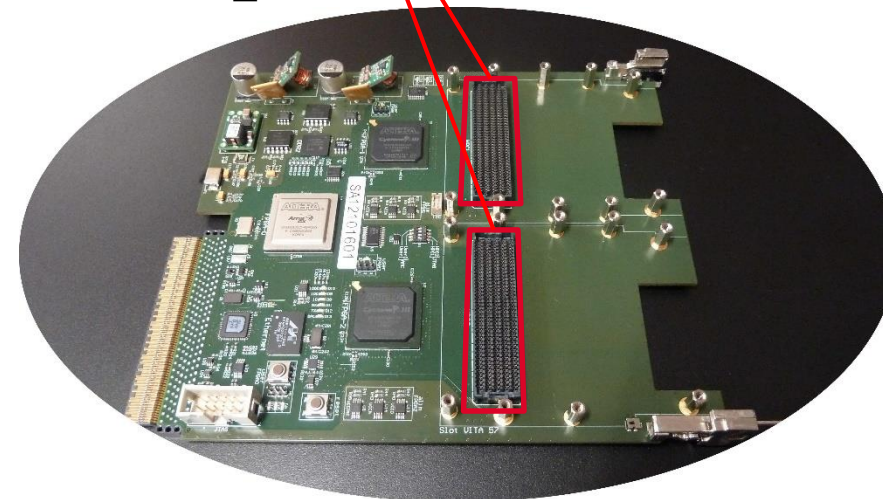
Electronics

- DDC family is already used in Nuclear Instrumentation
- CAMEL Board by LPC (Caen, France)
 - <http://faster.in2p3.fr/>
- CAMEL → 2 × DDC316
 - 32 channels
 - 16 bits
 - Range: 3pC up to 12 pC
 - 10 μ s to 1 ms
- μ TCA solution:
 - CAMEL (DAQ)
 - SYROCO_AMC (CS)

CAMEL




SYROCO_AMC



Electronics (Noise)

- Noise with DDC depending on:
 - Range selected
 - Sensor capacitance
- Example with DDC316 (see Table)
- Signal is in noise

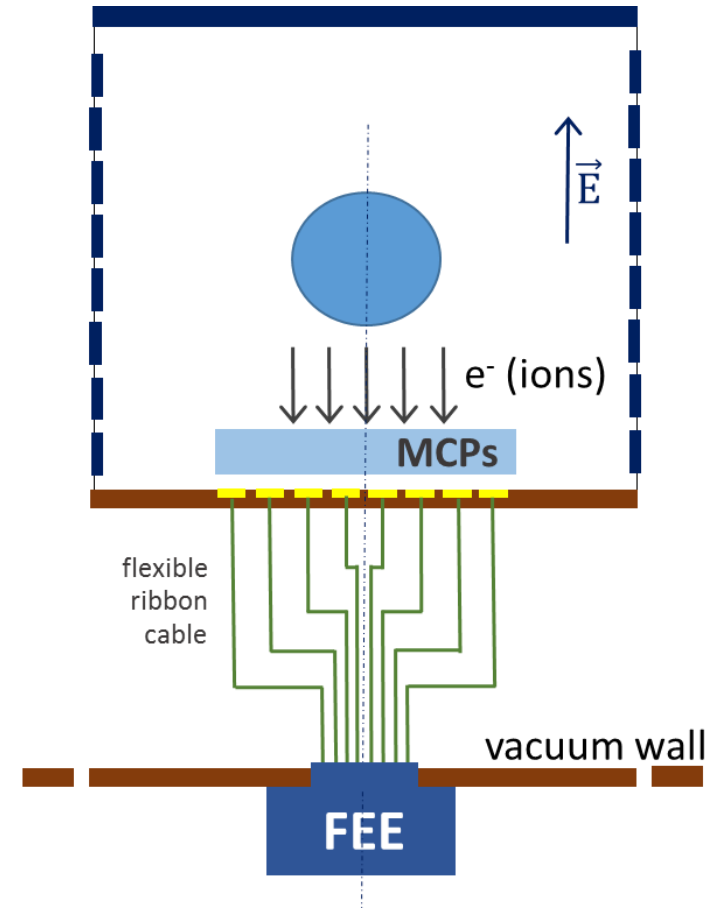
To go away from vacuum (and rads)
2 meters of cable ~ 100pF



Range selected	Noise in fC ($C_{\text{sensor}} = 20\text{pF}$)	Noise in fC ($C_{\text{sensor}} = 50\text{pF}$)	Noise in fC ($C_{\text{sensor}} = 100\text{pF}$)
-0.046 to 3pC	0.6	1	1.57
-0.18 to 12pC	0.93	1.17	1.7

Principle of operation

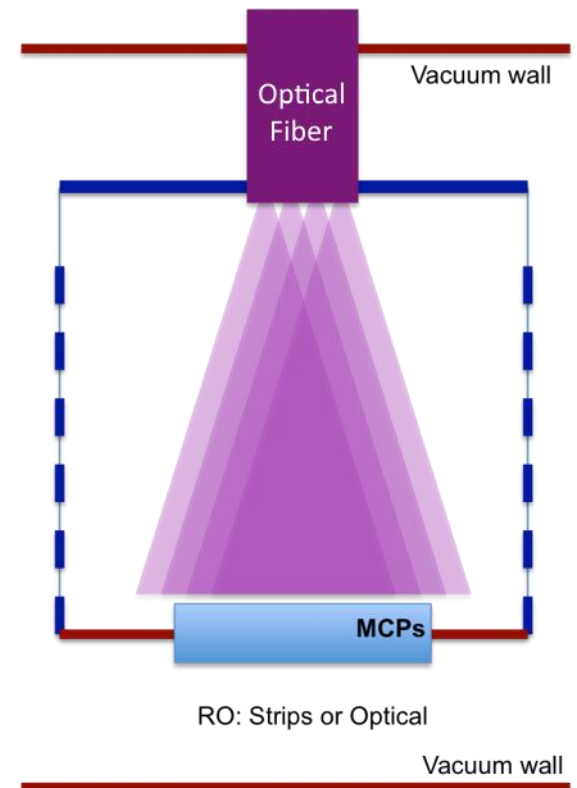
- MCP multiplies ions/electrons
- Use MCP to increase signal on strips
- Typical gain of a MCP:
 - Single: 10^4
 - Double (stack): 10^6
- For 4fC as MCP input $\rightarrow 4 \times 10^4 \times 0.6 = 24\text{pC}$
- So readout electronic can be the same as previously !



MCP Ageing

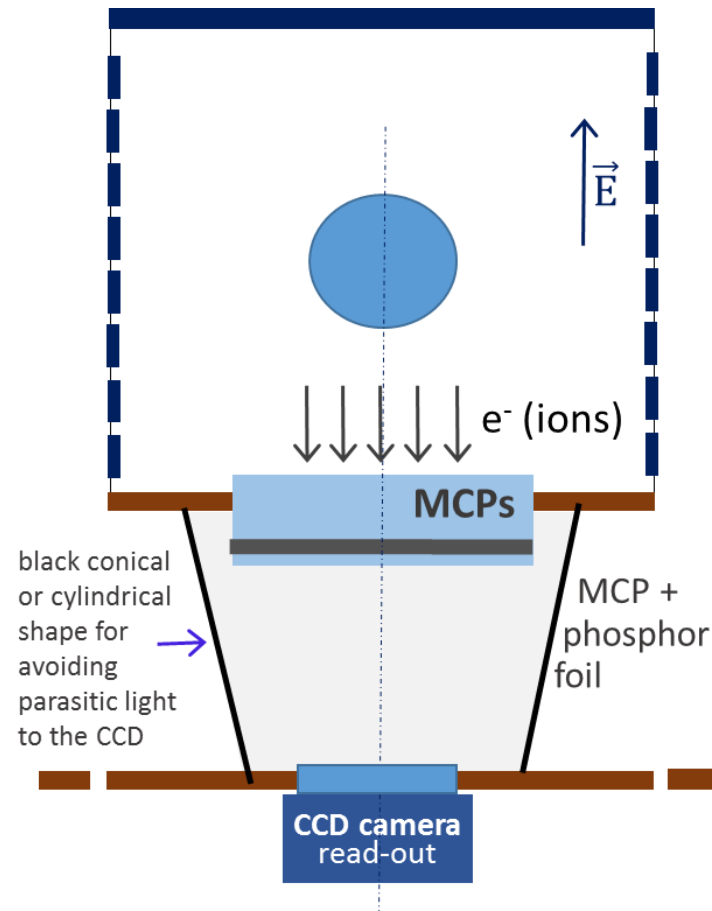
- MCP drawback: Ageing
- Depending of gain
- Data on ageing from Hamamatsu
- E.g. gain: 10^4 , at 90MeV: 105k ions/e-
 - At $t = 0$ gain = 100%
 - At $t = 1,4$ years gain start to decrease
 - At $t = 14$ years gain = 80%
 - **Gain should be optimized**
- A calibration system is also considered
 - Uniform UV light + OF
 - RO offline correction

Calibration system



Principle of operation

- Use phosphor screen instead strips (P-MCP)
- Phosphor screen: electrons \rightarrow light
- Shield against background photons
- Camera can be deported with coherent OF bundle
 - To be define (radiations, location)
- Calibration also required
 - P-MCP ageing

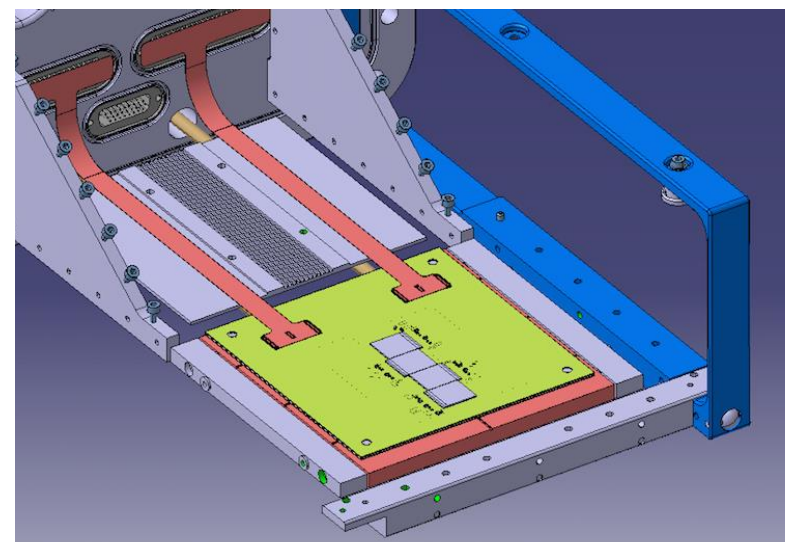
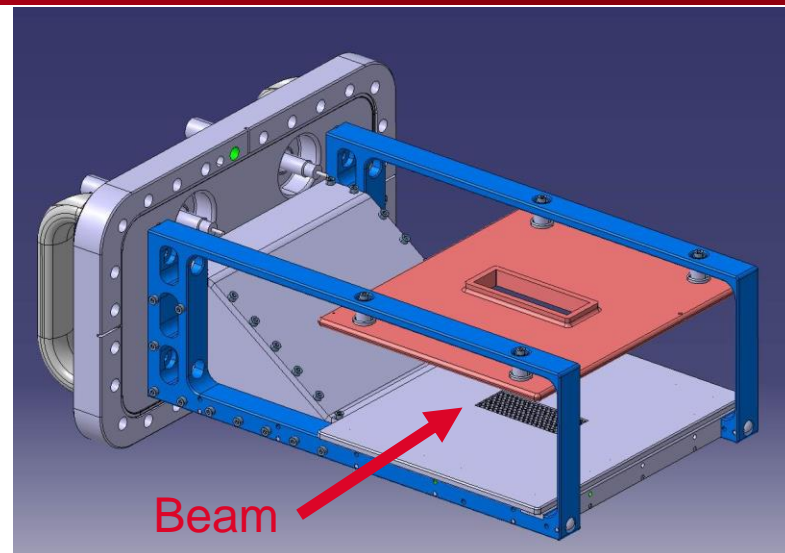


PS NPM (PS-BGI)

- Project for the PS at CERN
- 4 Timepix3 = 56.3mm x 14mm total surface
- High sensitive and fast NPM
- 55 μ m spatial resolution
- Cooling system are required
- Collaboration since October 2016

Storey, J.; Bodart, D.; Dehning, B.; Levasseur, S.; Pacholek, P.; Rakai, A.; Sapinski, M.; Schneider, G.; Steyart, D. & Satou, K.

Development of an Ionization Profile Monitor Based on a Pixel Detector for the CERN Proton Synchrotron
IBIC2015, Melbourne, Australia, 2015

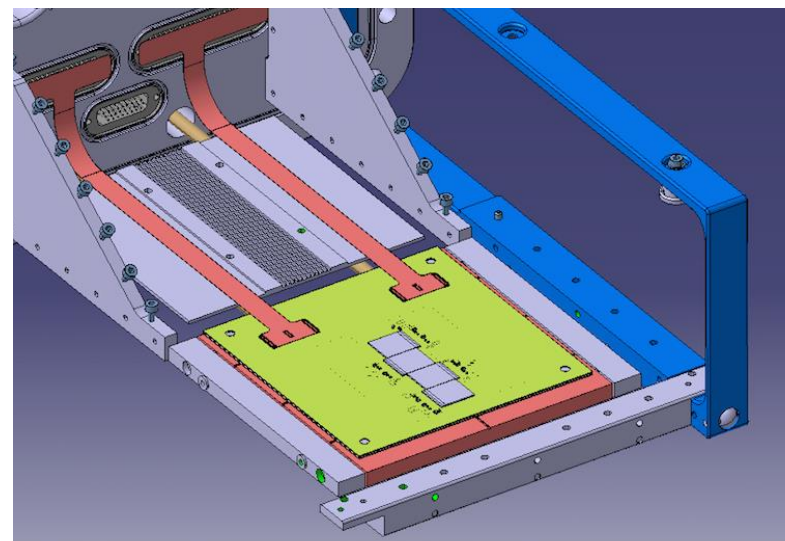
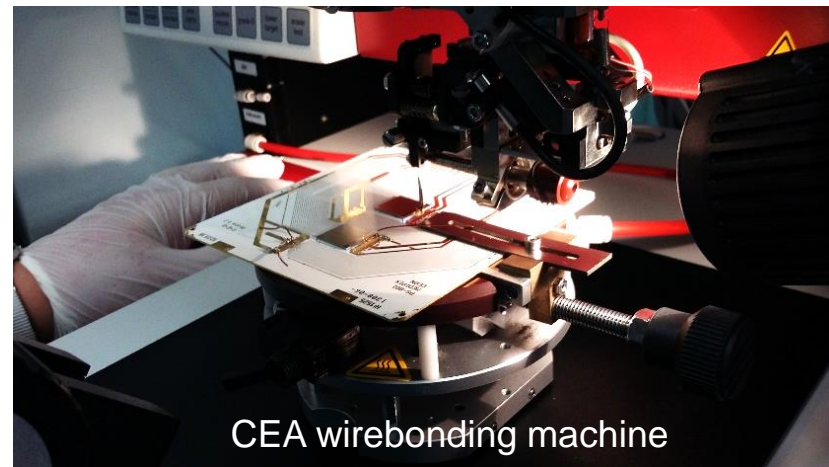


Collaboration

- Process is difficult
 - Complex PCB vacuum compatible
 - 100 wirebonding per chips
 - Critical chips placement

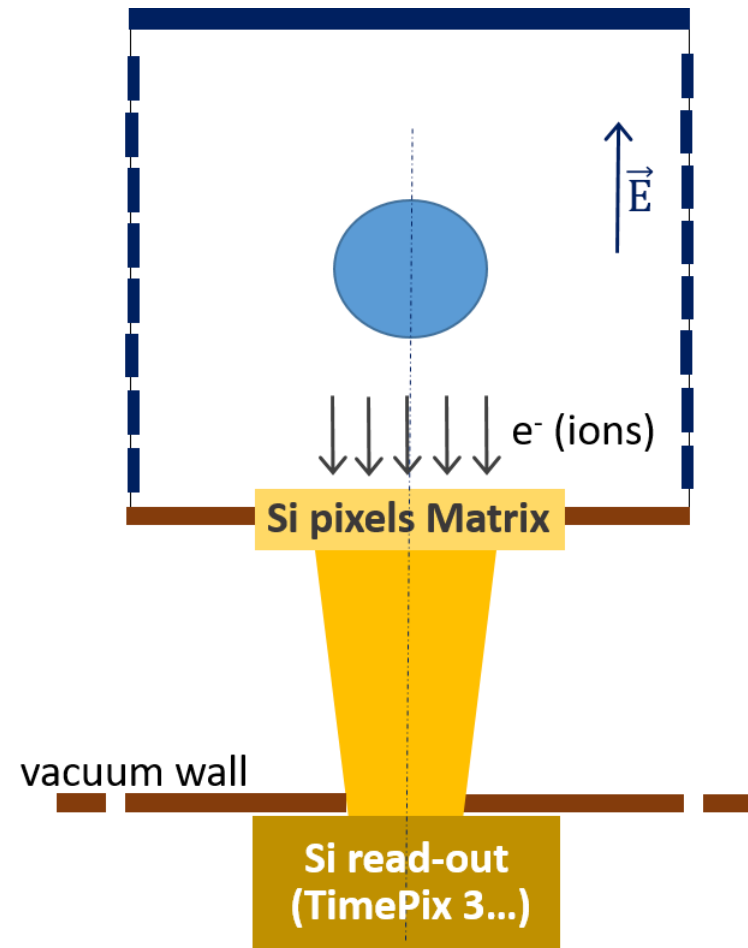
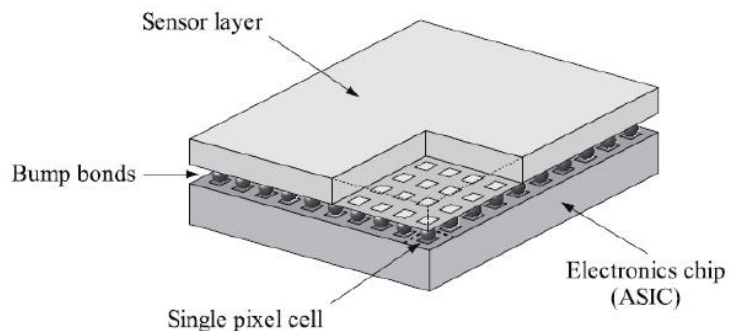
- CERN Team provide us:
 - A lot of information
 - A PCB

- Wirebonding at CEA-Saclay if possible:
 - Gold bonding on TP1 → OK
 - Next attempts on TP3
 - Try to perform reliable and automatic process



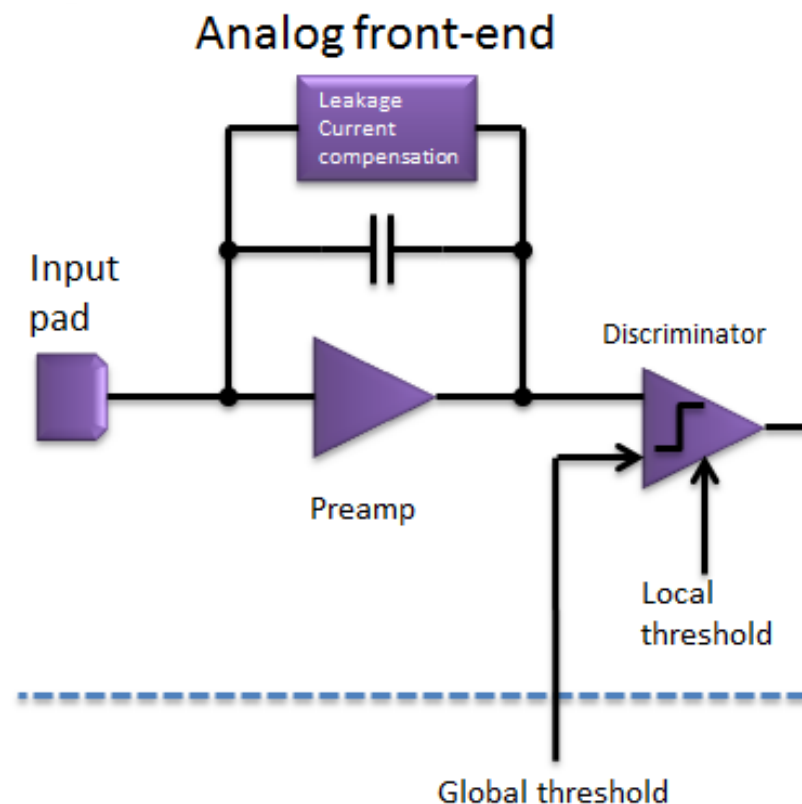
Silicon sensor

- Silicon pixelated detector
 - Great spatial resolution
 - Silicon is versatile SC
- 1 electron at 5keV → 1400 pairs in silicon
- Ions at keV are completely stop in few hundred nm
 - **To be tested !**



TimePix3

- 256x256 55 μ m pixel readout chip for Hybrid Pixel Detector
- Still work after 4.5 MGy
- Noise is about 500 electrons
- Three different measure modes:
 - Time of Arrival
 - ToA + Time over Threshold
 - ToT + Events counting
- Two different read modes:
 - Frame based
 - Data driven



TimePix3

- Maximum hit rate without dead time:

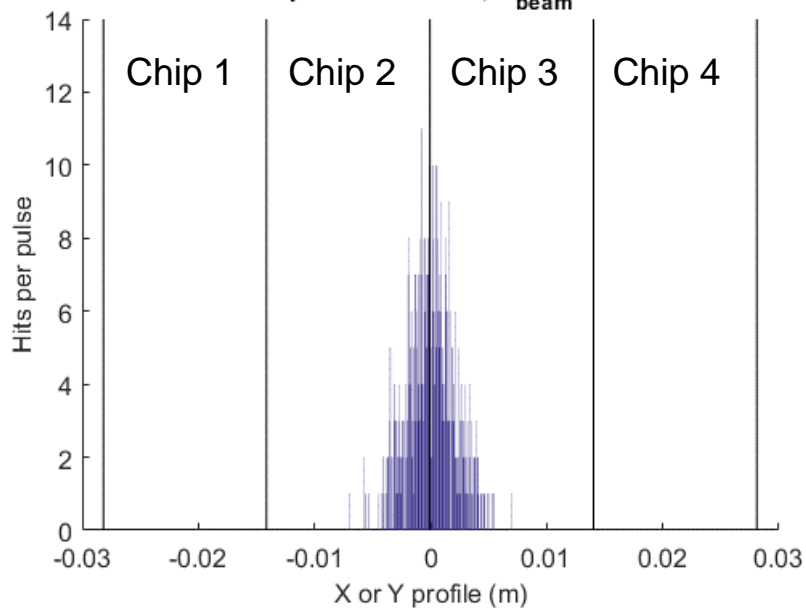
- 80 MHits/s per chip

- 50 kHits/s per pixel

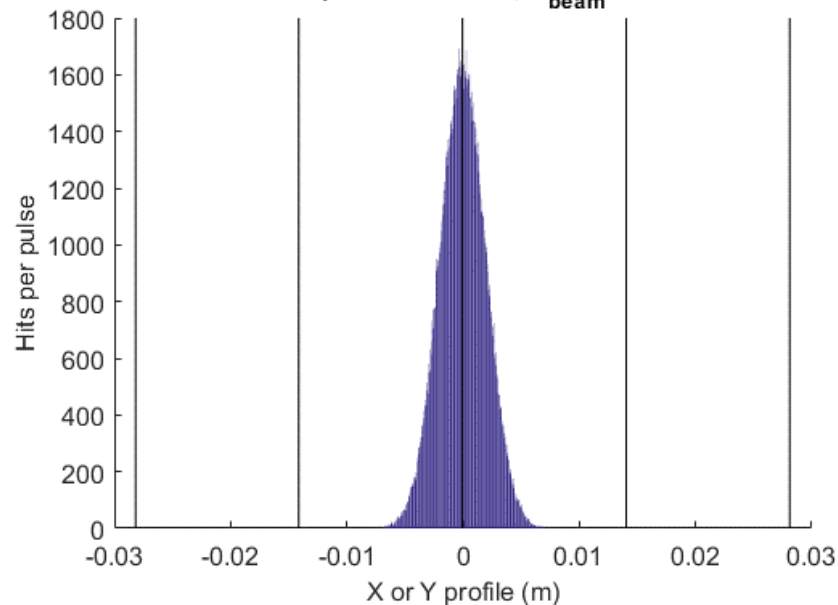
- ~140 pixels are hit more than once/pulse

- 5kHits/s max per pixel

Hits on one row of four Timepix3 chips, each bin equal to a pixel
For one pulse at 90 MeV, $\sigma_{\text{beam}} = 2 \text{ mm}$



Hits on four Timepix3 chips, each bin equal to a pixel
For one pulse at 90 MeV, $\sigma_{\text{beam}} = 2 \text{ mm}$



Electronics

- TimePix3 need a CS electronics
- FitPix: Commercial solution
 - Advacam/WidePix
 - General purpose use → Limited
 - We will use it for tests
- CERN Team custom solution
 - In development
 - Based on GEFE Board
 - Dedicated to NPM usage

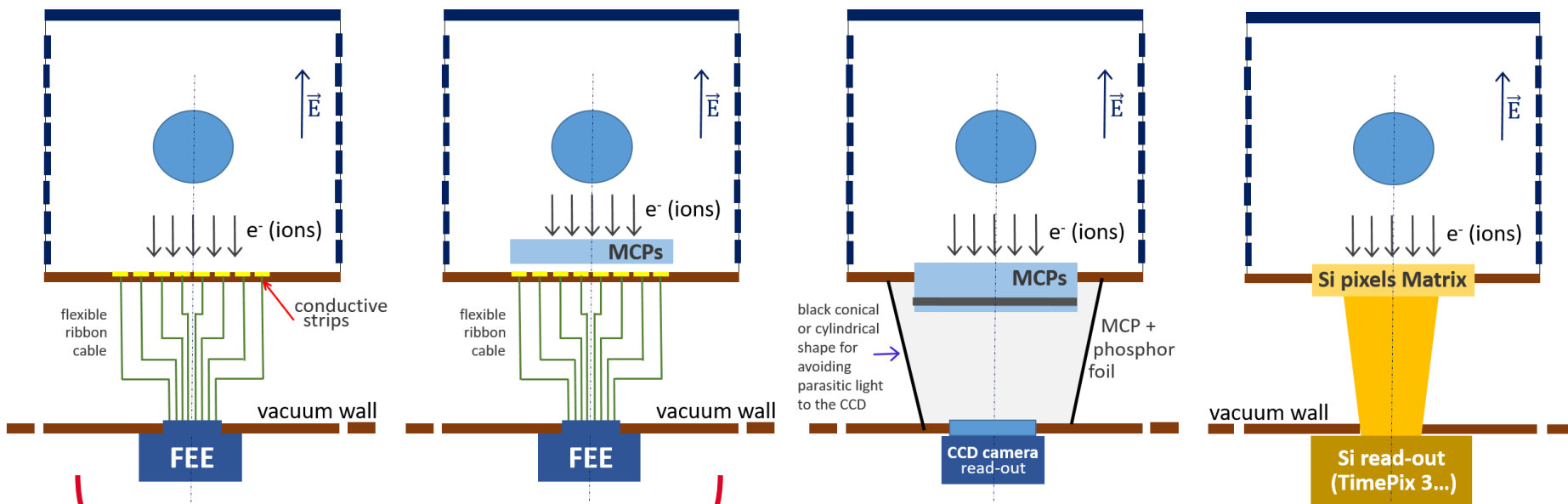


<http://www.ohwr.org/projects/gefe/>



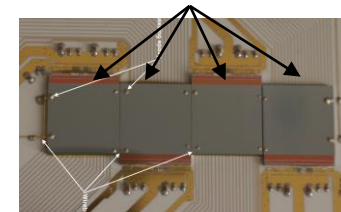
CONCLUSION - SUMMARIZE

cea CONCLUSION - SUMMARIZE



TBD

4 Timepix 3 chips





THANKS FOR YOUR ATTENTION

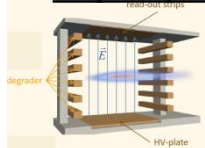
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QUESTIONS ?

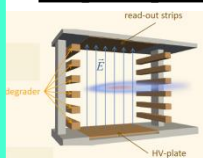


BACKUP SLIDES

Strip line profiler



Strip line profiler



microchannel plate (MPC)



+

70kV HT



BNC HT

Sub-D connector



Transimpedance readout amplifier ADC



Current-Input Analog-to-Digital Converter



Caramel



SYROCO_AMC



+

Timepix3



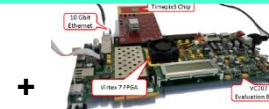
BNC HT Cooling Sub-D connector



GEFE



FitPIX



+

Optical

Double chevron microchannel plate (MPC)



Posphor foil

CCD Camera read-out



